AMENDMENTS TO THE SPECIFICATION:

The paragraph beginning on page 1, line 18 has been changed as follows:

Referring to FIG. 1A, a bottom low-dielectric insulating film 102 is formed on a silicon substrate 101 for which a given process is implemented. An anti-polishing layer 103 is then formed on the bottom low-dielectric insulating film 102. Next, the anti-polishing layer 103 and the bottom low-dielectric insulating film 102 are patterned to form a trench of a given depth. Thereafter, an anti-diffusion film 104 and a copper film ~~105~~ are sequentially formed on the entire structure. The copper film ~~105~~ and the anti-diffusion film 104 formed on the anti-polishing layer 103 are then removed by means of a chemical mechanical polishing (CMP) process, so copper wires 105 surrounded by the anti-diffusion film 104 are formed within the trench.

The paragraph beginning on page 2, line 21 has been changed as follows:

Referring to FIG. 1D, an anti-diffusion film ~~111~~ 11 and a copper film ~~112~~ (not shown) are sequentially formed on the entire structure including the trench 110 and the via hole 108. The copper film ~~112~~ and the anti-diffusion film ~~111~~ 11 deposited on the top low-dielectric insulating film ~~106e~~ 6e are then removed by means of a chemical mechanical polishing (CMP) process, so that copper wires ~~112~~ 12 surrounded by the anti-diffusion film ~~111~~ 11 is formed within the trench. The copper wires ~~112~~ 12 are connected to the copper wires 105 via the via hole 108.

The paragraph beginning on page 4, line 22 has been changed as follows:

A method of forming metal wires using a plate according to one embodiment of the present invention is characterized in that it comprises the steps of a) forming a low-dielectric insulating film on a silicon substrate for which given processes are implemented, and then

forming a trench in the low-dielectric insulating film; b) forming lower metal wires within the trench; c) adhering a plate ~~having a plate~~ in which a plurality of implantation holes are formed and a sidewall of a given height is formed at its edge, an engraved pattern for forming a plurality of trenches formed on the plate, and an engraved pattern for forming a plurality of via holes formed on the engraved pattern for forming the trench, onto a silicon substrate; d) implanting a low-dielectric insulating material through the implantation holes and then annealing the low-dielectric insulating material; e) removing the plate to obtain a low-dielectric insulating film pattern having the plurality of the trenches shaped by the engraved pattern for forming the trenches and the plurality of the via holes shaped by the engraved pattern for forming the via holes; and f) forming upper metal wires, which are connected to the lower metal wires through the via holes, within the trenches.

The paragraph beginning on page 5, line 15 has been changed as follows:

In another embodiment of the present invention, a method of forming metal wires using a plate is characterized in that it comprises the steps of a) forming a low-dielectric insulating film on a silicon substrate for which given processes are implemented and then forming a trench in the low-dielectric insulating film; b) forming lower metal wires within the trench; c) adhering a plate ~~having a plate~~ in which a plurality of first and second implantation holes are each formed and a sidewall of a given height is formed at its edge, an engraved pattern for forming a plurality of trenches formed on the plate, and an engraved pattern for forming a plurality of via holes formed on the engraved pattern for forming the trench, onto a silicon substrate; d) implanting a first insulating material of a given amount through the first implantation hole and then performing a first annealing process; e) implanting a second insulating material through the second implantation hole and then performing a second annealing process; f) removing the plate to obtain an insulating film pattern of a multi-layer

structure having the plurality of the trenches shaped by the engraved pattern for forming the trenches and the plurality of the via holes shaped by the engraved pattern for forming the via holes; and g) forming upper metal wires, which are connected to the lower metal wires through the via holes, within the trenches.

The paragraph beginning on page 8, line 23 has been changed as follows:

With reference to FIG. 3B, the plate 20 constructed ~~an~~ as in FIG. 2 is located on a silicon substrate 301. A proper pressure is applied to the plate 20 so that the sidewall 20b adheres closely to the edge of the silicon substrate 301. Only when the plate 20 and the silicon substrate 301 are completely sealed, a complete contact between the metal wires is accomplished and outside leakage of the insulating film is prevented.